L Number	Hits	Search Text	DB	Time stamp
-	207	(mfs MFMIS) with (ferroelectric	USPAT;	2002/06/05
		ferro-electric)	US-PGPUB;	12:44
			EPO; JPO;	12:44
			DERWENT;	
ļ			IBM TDB	
_	109	((mfs MFMIS) with (ferroelectric	USPAT;	2002/06/06
		ferro-electric)) and (writ\$3 program\$4)	US-PGPUB;	16:59
		and (read\$3)	EPO; JPO;	10.59
			DERWENT;	
			IBM TDB	
-	12		USPAT;	2002/06/05
		ferro-electric)) and (writ\$3 program\$4)	US-PGPUB;	13:58
		and (read\$3)) and ((current adj3 chang\$3)	EPO; JPO;	
		same (Vds voltage))	DERWENT;	
			IBM_TDB	
-	14498	(mfs MFMIS) (metal adj4 (ferroelectric	USPAT;	2002/06/05
		ferro-electric) adj4 insulator)	US-PGPUB;	13:06
			EPO; JPO;	
			DERWENT;	
_	3093	//mfg MEMTC) /makal alid /C	IBM_TDB	
-	3093	((mfs MFMIS) (metal adj4 (ferroelectric	USPAT;	2002/06/05
		ferro-electric) adj4 insulator)) and (writ\$3 program\$4) and (read\$3)	US-PGPUB;	13:08
	l	(wireys programs4) and (readss)	EPO; JPO;	
			DERWENT;	
_	29	(((mfs MFMIS) (metal adj4 (ferroelectric	IBM_TDB	2002/05/05
		ferro-electric) adj4 insulator)) and	USPAT; US-PGPUB;	2002/06/05
i		(writ\$3 program\$4) and (read\$3)) and	EPO; JPO;	12:55
		((current adj3 chang\$3) same (Vds	DERWENT;	
		voltage))	IBM TDB	
-	18496	(mfs MFIS MFMIS) (metal adj3	USPAT;	2002/06/05
		(ferroelectric ferro-electric) adj3	US-PGPUB;	13:07
		insulator)	EPO; JPO;	13.07
			DERWENT;	
İ			IBM TDB	
-	3302	((mfs MFIS MFMIS) (metal adj3	USPAT;	2002/06/05
		(ferroelectric ferro-electric) adj3	US-PGPUB;	13:09
		insulator)) and (writ\$3 program\$4) and	EPO; JPO;	
		(read\$3)	DERWENT;	
	20	111 6 2000	IBM_TDB	
_	29	(((mfs MFIS MFMIS) (metal adj3	USPAT;	2002/06/06
		(ferroelectric ferro-electric) adj3	US-PGPUB;	16:58
		insulator)) and (writ\$3 program\$4) and	EPO; JPO;	
		(read\$3)) and ((current adj3 chang\$3) same (Vds voltage))	DERWENT;	
_	10	(((mfs MFIS MFMIS) (metal adj3	IBM_TDB USPAT;	2002/06/06
	10	(ferroelectric ferro-electric) adj3	USPAT; US-PGPUB;	2002/06/06 16:55
		insulator)) and (writ\$3 program\$4) and	EPO; JPO;	10.55
		(read\$3)) and ((current adj3 chang\$3)	DERWENT;	
		same (Vds voltage)) and (ferroelectric	IBM TDB	
		adj3 capacitor)		
-	10	((((mfs MFIS MFMIS) (metal adj3	USPAT;	2002/06/06
		(ferroelectric ferro-electric) adj3	US-PGPUB;	16:55
	Ì	insulator)) and (writ\$3 program\$4) and	EPO; JPO;	
		(read\$3)) and ((current adj3 chang\$3)	DERWENT;	
		same (Vds voltage)) and (ferroelectric	IBM TDB	
		adj3 capacitor)) and (gate adj3	_	
	_	electrode)		
-	4	(((mfs MFIS MFMIS) (metal adj3	USPAT;	2002/06/06
		(ferroelectric ferro-electric) adj3	US-PGPUB;	17:00
		insulator)) and (writ\$3 program\$4) and	EPO; JPO;	
		(read\$3)) and ((current adj3 chang\$3)	DERWENT;	
		same (Vds voltage)) and ((ferroelectric adj3 capacitor) with (gate adj3	IBM_TDB	
		electrode))		
		5155515de/)		F I

	205	1/fannalastus = 322		
-	203	((ferroelectric adj3 capacitor) with	USPAT;	2002/06/06
	İ	(gate adj3 electrode))	US-PGPUB;	16:58
			EPO; JPO;	
			DERWENT;	
	40	///fammanlandmin - 4:2	IBM_TDB	
-	40		USPAT;	2002/06/06
		(gate adj3 electrode))) and (mfs MFIS	US-PGPUB;	16:58
		MFMIS)	EPO; JPO;	
			DERWENT;	
	22	11115	IBM_TDB	
-	32		USPAT;	2002/06/06
1		(gate adj3 electrode))) and (mfs MFIS	US-PGPUB;	17:00
	1	MFMIS)) and (writ\$3 program\$4) and	EPO; JPO;	1
		(read\$3)	DERWENT;	
	1	111115	IBM_TDB	
-	16		USPAT;	2002/06/06
		(gate adj3 electrode))) and (mfs MFIS	US-PGPUB;	17:00
		MFMIS)) and (writ\$3 program\$4) and	EPO; JPO;	
		(read\$3)) and ((ferroelectric	DERWENT;	
		ferro-electric) adj3 insulator)	IBM_TDB	
-	5690	read\$3 same ((voltage potential bias)	USPAT;	2003/03/20
		with drain with source)	US-PGPUB;	11:17
	1		EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	574	((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)	US-PGPUB;	12:17
			EPO; JPO;	
	1		DERWENT;	
			IBM TDB	1
-	22		USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:19
		(nonvolatile non-volatile)	EPO; JPO;	
			DERWENT;	
			IBM TDB	ĺ
-	2835	(read\$3 same ((voltage potential bias)	USPAT;	2003/03/20
:		with drain with source)) and (nonvolatile	US-PGPUB;	11:20
		non-volatile)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	5	((((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:23
		(nonvolatile non-volatile)) and ((read\$3	EPO; JPO;	111.23
		same ((voltage potential bias) with drain	DERWENT;	
		with source)) and (nonvolatile	IBM_TDB	
		non-volatile))		
-	124614	((MFS MFMIS ferroelectric) near3	USPAT;	2003/03/20
		transistor) FeRAM non-volatile	US-PGPUB;	11:25
		nonvolatile	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	22		USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:25
		(((MFS MFMIS ferroelectric) near3	EPO; JPO;	
		transistor) FeRAM non-volatile	DERWENT;	
		nonvolatile)	IBM TDB	
-	1		USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:27
		(((MFS MFMIS ferroelectric) near3	EPO; JPO;	
		transistor) FeRAM non-volatile	DERWENT;	
1		nonvolatile)) and ((read\$3 with data with	IBM TDB	
		(appl\$3 near3 (voltage bias potential))	-2100	
	' İ	with source with drain))		
]]	(((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
1	_	region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:27
		((read\$3 with data with (appl\$3 near3	EPO; JPO;	+1.4/
		(voltage bias potential)) with source	DERWENT;	
		with drain))	· ·	
	L		IBM_TDB	

_	224	(read\$3 with data with (appl\$3 near3	Trans-	
_	224	(voltage bias potential)) with source	USPAT;	2003/03/20
		with drain)	US-PGPUB;	11:30
		with drain,	EPO; JPO;	
			DERWENT;	
-	181	(((MFS MFMIS ferroelectric) near3	IBM_TDB USPAT;	2003/03/20
		transistor) FeRAM non-volatile	US-PGPUB;	2003/03/20
		nonvolatile) and ((read\$3 with data with	EPO; JPO;	12:16
		(appl\$3 near3 (voltage bias potential))	DERWENT;	
		with source with drain))	IBM TDB	
-	1		USPĀT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:29
		((((MFS MFMIS ferroelectric) near3	EPO; JPO;	
	•	transistor) FeRAM non-volatile	DERWENT;	
Ì		nonvolatile) and ((read\$3 with data with	IBM_TDB	
		(appl\$3 near3 (voltage bias potential))		
	1660	with source with drain)))		
-	1669		USPAT;	2003/03/20
		potential)) with source with drain)	US-PGPUB;	11:33
			EPO; JPO;	
			DERWENT;	
-	3	(((unsaturat\$3 non-saturat\$3) near3	IBM_TDB	2002/02/02
	1	region) and (saturat\$3 near3 region)) and	USPAT; US-PGPUB;	2003/03/20
		(read\$3 same ((appl\$3 near3 (voltage bias	EPO; JPO;	11:45
		potential)) with source with drain))	DERWENT;	
1		Salara S	IBM TDB	
1 -	11	((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
İ		region) with read\$3	US-PGPUB;	11:53
	1		EPO; JPO;	11.00
			DERWENT;	
	İ		IBM TDB	
-	1	((() Included the state of the state	USPAT;	2003/03/20
		region) with read\$3) and (non-volatile	US-PGPUB;	11:52
		nonvolatile)	EPO; JPO;	
			DERWENT;	
	3769	(manahamata)	IBM_TDB	
_	3/69	(unsaturat\$3 non-saturat\$3) with read\$3	USPAT;	2003/03/20
			US-PGPUB;	11:53
		·	EPO; JPO;	
			DERWENT; IBM_TDB	
_	3779	(unsaturat\$3 non-saturat\$3 nonsaturat\$3)	USPAT;	2003/03/20
		with read\$3	US-PGPUB;	11:53
			EPO; JPO;	11.55
			DERWENT;	
1 .			IBM TDB	
-	200	((unsaturat\$3 non-saturat\$3 nonsaturat\$3)	USPAT;	2003/03/20
		with read\$3) and (non-volatile	US-PGPUB;	11:54
		nonvolatile)	EPO; JPO;	
			DERWENT;	
	222	///MEDG MEDICE C	IBM_TDB	
_	200	(((USPAT;	2003/03/20
		transistor) FeRAM non-volatile	US-PGPUB;	12:04
		nonvolatile) and (((unsaturat\$3	EPO; JPO;	
		non-saturat\$3 nonsaturat\$3) with read\$3) and (non-volatile nonvolatile))	DERWENT;	
_	28	((((MFS MFMIS ferroelectric) near3	IBM_TDB	3003/03/30
	20	transistor) FeRAM non-volatile	USPAT; US-PGPUB;	2003/03/20
		nonvolatile) and (((unsaturat\$3	EPO; JPO;	12:09
		non-saturat\$3 nonsaturat\$3) with read\$3)	DERWENT;	
		and (non-volatile nonvolatile))) and	IBM TDB	
		(read reading)	-2100	
[-	8	((((MFS MFMIS ferroelectric) near3	USPAT;	2003/03/20
		transistor) FeRAM non-volatile	US-PGPUB;	12:09
		nonvolatile) and (((unsaturat\$3	EPO; JPO;	
]		non-saturat\$3 nonsaturat\$3) with read\$3)	DERWENT;	
		and (non-volatile nonvolatile))) and	IBM_TDB	
		(read reading)) and memory		

-	1	((read\$3 with data with (appl\$3 near3	USPAT;	2003/03/20
		(voltage bias potential)) with source	US-PGPUB;	12:19
		with drain)) and ((unsaturat\$3	EPO; JPO;	
	Ì	non-saturat\$3 nonsaturat\$3) near3 region)	DERWENT;	
			IBM_TDB	
-	1	read\$3 with (unsaturat\$3 non-saturat\$3	USPAT;	2003/03/20
		nonsaturat\$3) with (current near3	US-PGPUB;	12:20
		detect\$3)	EPO; JPO;	
			DERWENT;	
			IBM TDB	